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(54) Improvements in or relating to semiconductors

(57) A method is provided for silicon oxide etching for semiconductor manufacture including rinsing an etched silicon wafer by conducting a stream of deionized liquid water onto a spinning silicon wafer and contacting the deionized water with anhydrous hydrogen fluoride gas, hydrogen chloride gas, ozone, or mixtures thereof.

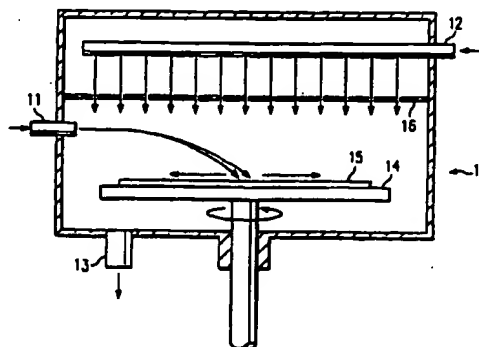


Figure 1.

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